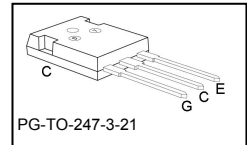
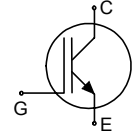


### Low Loss IGBT in TrenchStop® and Fieldstop technology

- Very low  $V_{CE(sat)}$  1.5 V (typ.)
- Maximum Junction Temperature 175 °C
- Short circuit withstand time – 5µs
- Designed for :
  - Frequency Converters
  - Uninterrupted Power Supply
- TrenchStop® and Fieldstop technology for 600 V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
  - very high switching speed
- Positive temperature coefficient in  $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Qualified according to JEDEC<sup>1</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	$V_{CE}$	$I_C$	$V_{CE(sat), T_j=25^\circ C}$	$T_{j,max}$	Marking	Package
IGW75N60T	600V	75A	1.5V	175°C	G75T60	PG-TO-247-3-21

#### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	600	V
DC collector current, limited by $T_{j,max}$	$I_C$		A
$T_C = 25^\circ C$		150	
$T_C = 100^\circ C$		75	
Pulsed collector current, $t_p$ limited by $T_{j,max}$	$I_{C,puls}$	225	
Turn off safe operating area ( $V_{CE} \leq 600V, T_j \leq 175^\circ C$ )	-	225	
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Short circuit withstand time <sup>2)</sup>	$t_{SC}$	5	µs
$V_{GE} = 15V, V_{CC} \leq 400V, T_j \leq 150^\circ C$			
Power dissipation $T_C = 25^\circ C$	$P_{tot}$	428	W
Operating junction temperature	$T_j$	-40...+175	°C
Storage temperature	$T_{stg}$	-55...+175	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

<sup>1</sup> J-STD-020 and JESD-022

<sup>2)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

### Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		0.35	K/W
Thermal resistance, junction – ambient	$R_{thJA}$		40	

### Electrical Characteristic, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.2mA$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=75A$ $T_j=25\text{ °C}$ $T_j=175\text{ °C}$	-	1.5	2.0	
			-	1.9	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=1.2mA, V_{CE}=V_{GE}$	4.1	4.9	5.7	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=600V, V_{GE}=0V$ $T_j=25\text{ °C}$ $T_j=175\text{ °C}$	-	-	40	$\mu A$
			-	-	1000	
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=75A$	-	41	-	S
Integrated gate resistor	$R_{Gint}$			-		$\Omega$

### Dynamic Characteristic

Input capacitance	$C_{iss}$	$V_{CE}=25V, V_{GE}=0V, f=1MHz$	-	4620	-	pF
Output capacitance	$C_{oss}$		-	288	-	
Reverse transfer capacitance	$C_{rss}$		-	137	-	
Gate charge	$Q_{Gate}$	$V_{CC}=480V, I_C=75A, V_{GE}=15V$	-	470	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	13	-	nH
Short circuit collector current <sup>1)</sup>	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 5\mu s, V_{CC}=400V, T_j\leq 150\text{ °C}$	-	687.5	-	A

<sup>1)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

### Switching Characteristic, Inductive Load, at $T_j=25\text{ °C}$

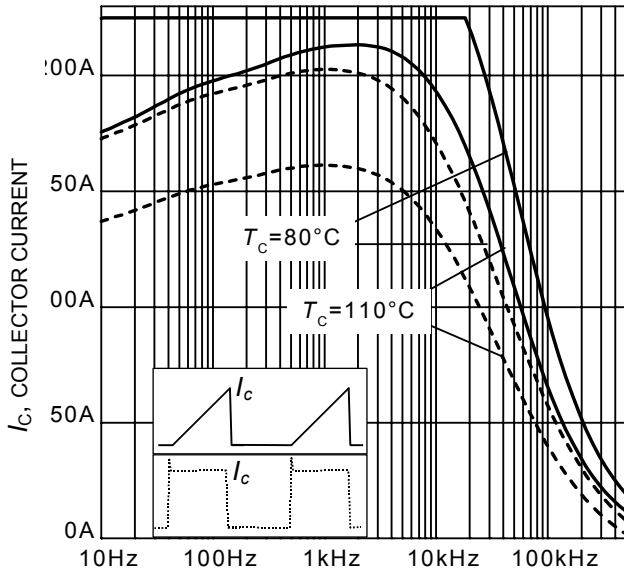
Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25\text{ °C}$ , $V_{CC}=400\text{V}$ , $I_C=75\text{A}$ , $V_{GE}=0/15\text{V}$ , $R_G=5\Omega$ , $L_{\sigma}^{(2)}=100\text{nH}$ , $C_{\sigma}^{(2)}=39\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	33	-	ns
Rise time	$t_r$		-	36	-	
Turn-off delay time	$t_{d(off)}$		-	330	-	
Fall time	$t_f$		-	35	-	
Turn-on energy <sup>1)</sup>	$E_{on}$		-	2.0	-	mJ
Turn-off energy	$E_{off}$		-	2.5	-	
Total switching energy	$E_{ts}$		-	4.5	-	

### Switching Characteristic, Inductive Load, at $T_j=175\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=175\text{ °C}$ , $V_{CC}=400\text{V}$ , $I_C=75\text{A}$ , $V_{GE}=0/15\text{V}$ , $R_G=5\Omega$ , $L_{\sigma}^{(2)}=100\text{nH}$ , $C_{\sigma}^{(2)}=39\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	32	-	ns
Rise time	$t_r$		-	37	-	
Turn-off delay time	$t_{d(off)}$		-	363	-	
Fall time	$t_f$		-	38	-	
Turn-on energy <sup>1)</sup>	$E_{on}$		-	2.9	-	mJ
Turn-off energy	$E_{off}$		-	2.9	-	
Total switching energy	$E_{ts}$		-	5.8	-	

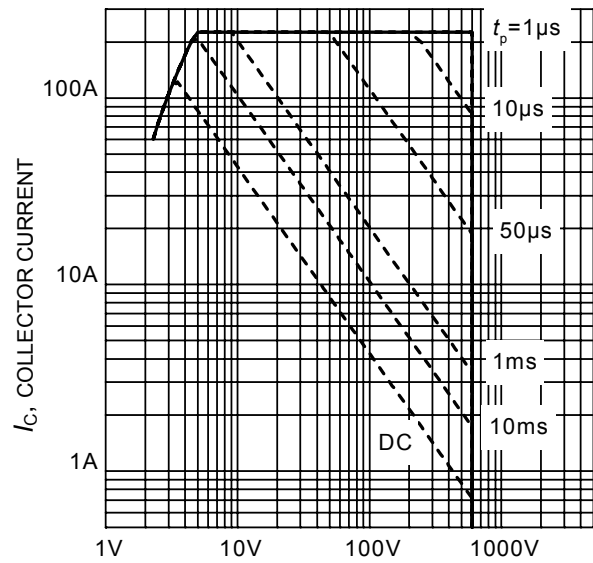
<sup>1)</sup> Includes Reverse Recovery Losses from IKW75N60T due to dynamic test circuit in Figure E.

<sup>2)</sup> Leakage inductance  $L_{\sigma}$  and Stray capacity  $C_{\sigma}$  due to dynamic test circuit in Figure E.



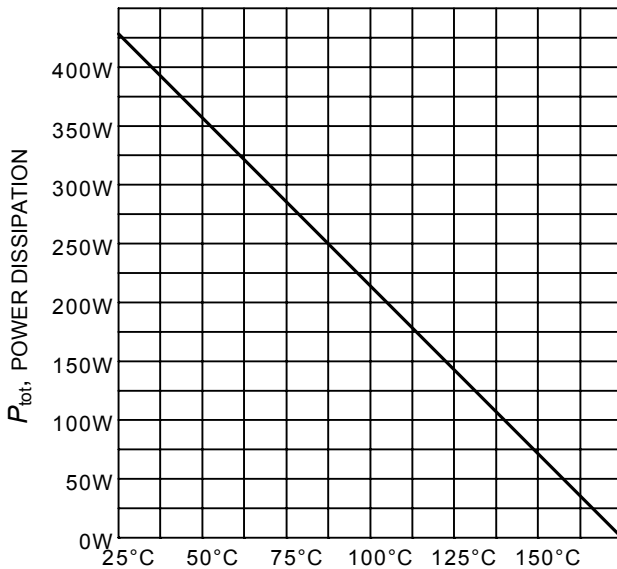
$f$ , SWITCHING FREQUENCY

**Figure 1. Collector current as a function of switching frequency**  
 ( $T_j \leq 175^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 400\text{V}$ ,  
 $V_{GE} = 0/+15\text{V}$ ,  $R_G = 5\Omega$ )



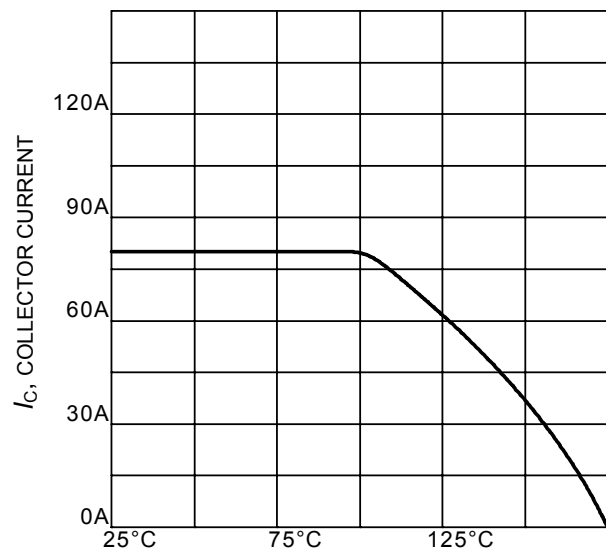
$V_{CE}$ , COLLECTOR-EMITTER VOLTAGE

**Figure 2. Safe operating area**  
 ( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 175^\circ\text{C}$ ;  
 $V_{GE} = 15\text{V}$ )



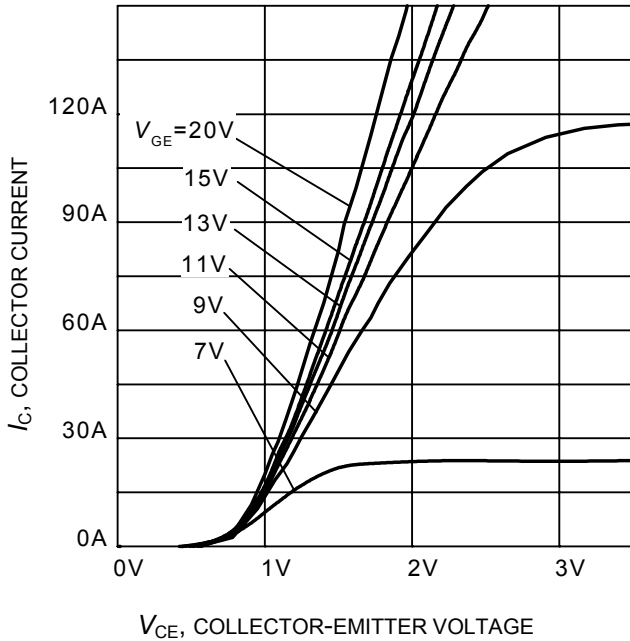
$T_C$ , CASE TEMPERATURE

**Figure 3. Power dissipation as a function of case temperature**  
 ( $T_j \leq 175^\circ\text{C}$ )

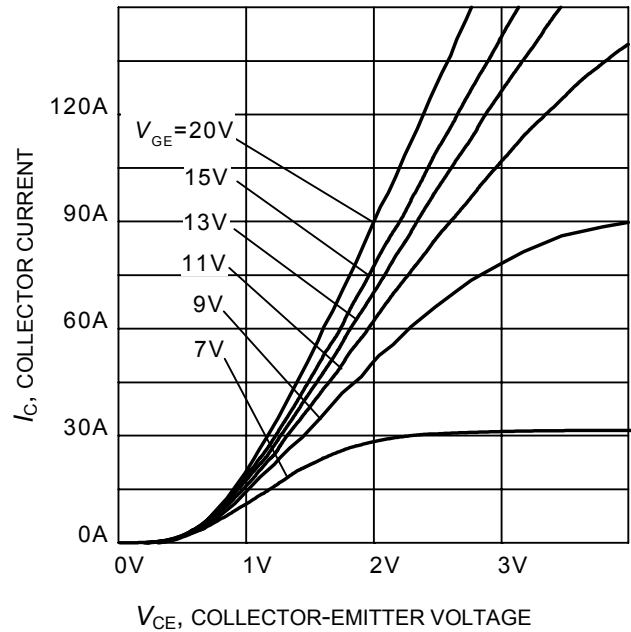


$T_C$ , CASE TEMPERATURE

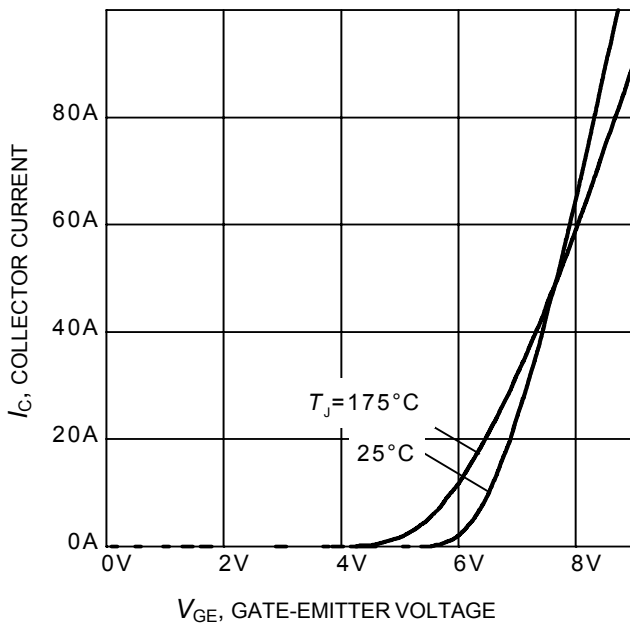
**Figure 4. DC Collector current as a function of case temperature**  
 ( $V_{GE} \geq 15\text{V}$ ,  $T_j \leq 175^\circ\text{C}$ )



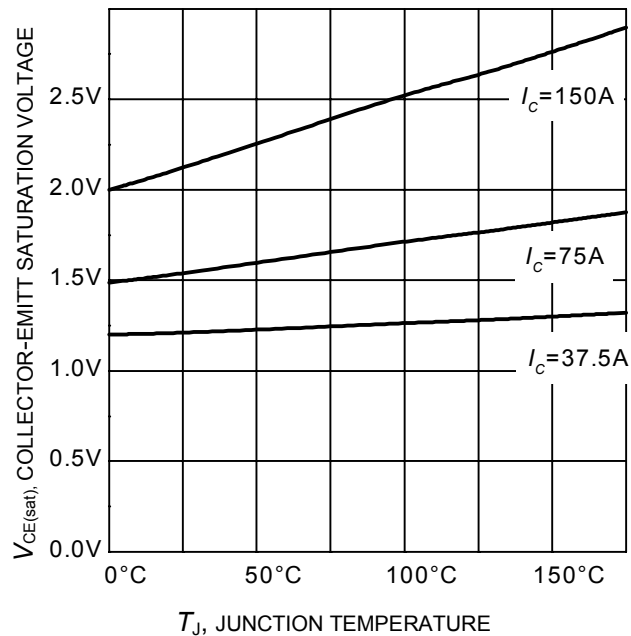
**Figure 5. Typical output characteristic**  
( $T_j = 25^\circ\text{C}$ )



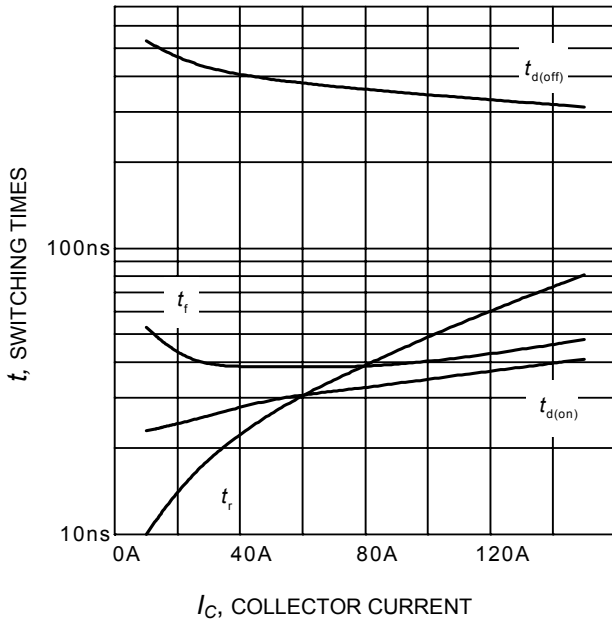
**Figure 6. Typical output characteristic**  
( $T_j = 175^\circ\text{C}$ )



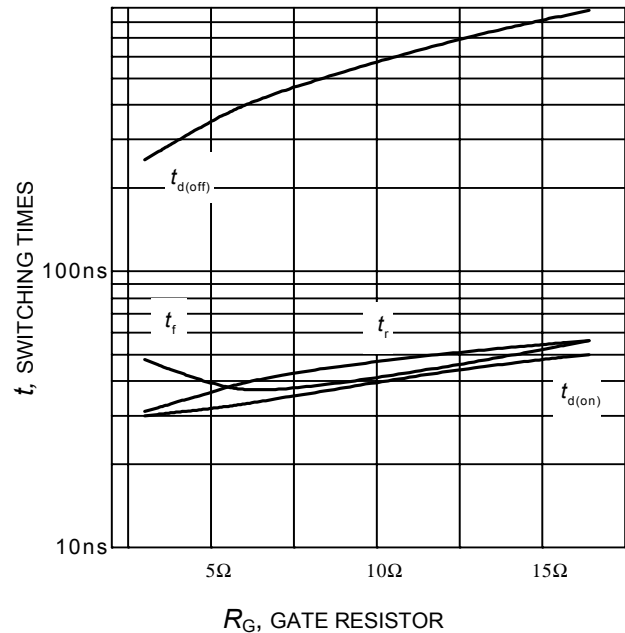
**Figure 7. Typical transfer characteristic**  
( $V_{CE} = 20\text{V}$ )



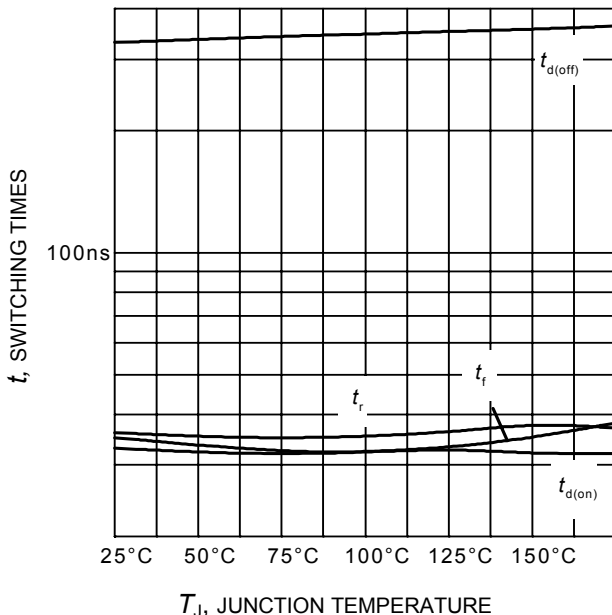
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



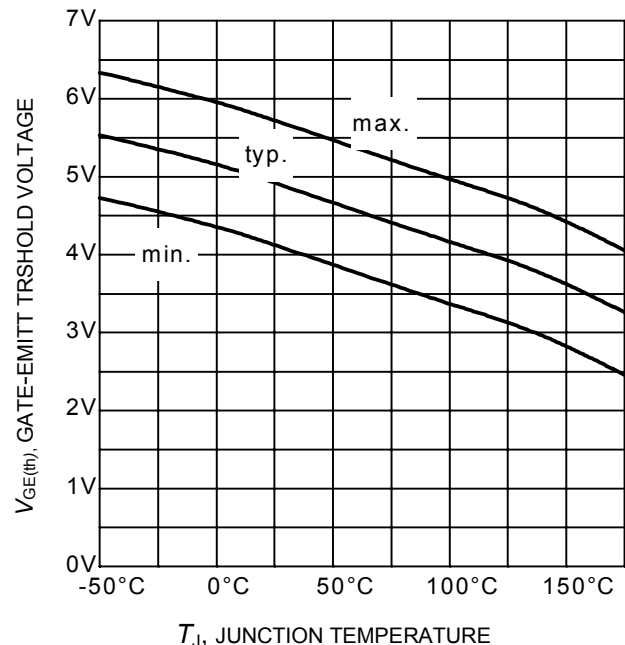
**Figure 9. Typical switching times as a function of collector current**  
(inductive load,  $T_J=175^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $R_G = 5\Omega$ , Dynamic test circuit in Figure E)



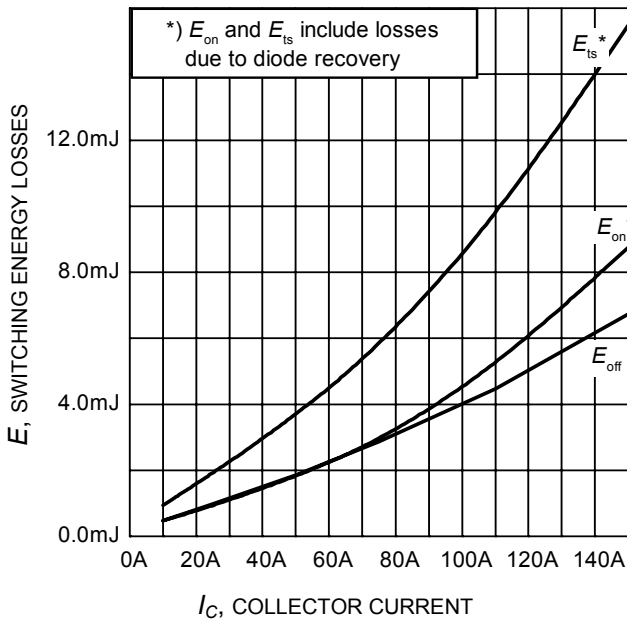
**Figure 10. Typical switching times as a function of gate resistor**  
(inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 75\text{A}$ , Dynamic test circuit in Figure E)



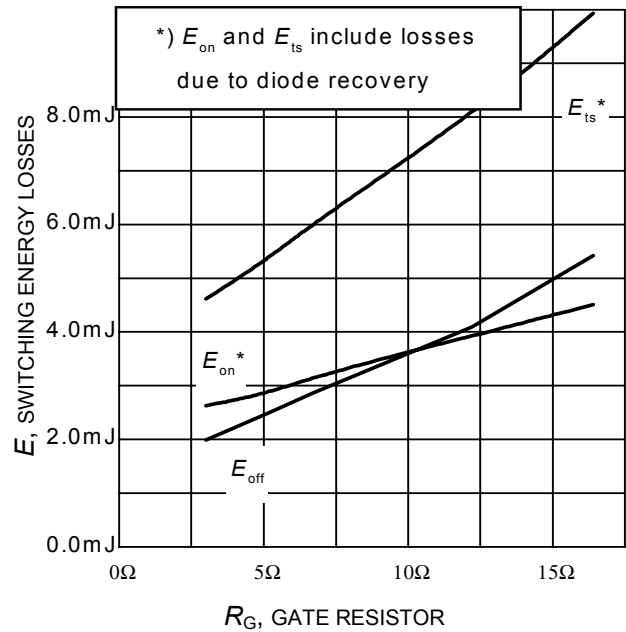
**Figure 11. Typical switching times as a function of junction temperature**  
(inductive load,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 75\text{A}$ ,  $R_G = 5\Omega$ , Dynamic test circuit in Figure E)



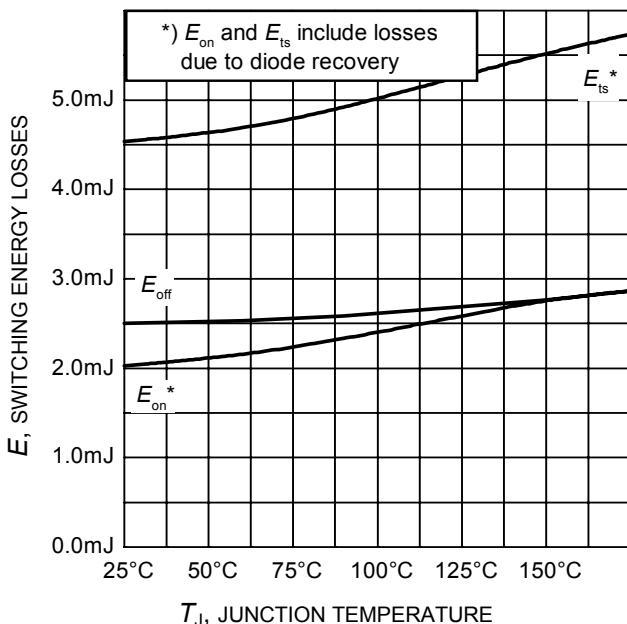
**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
( $I_C = 1.2\text{mA}$ )



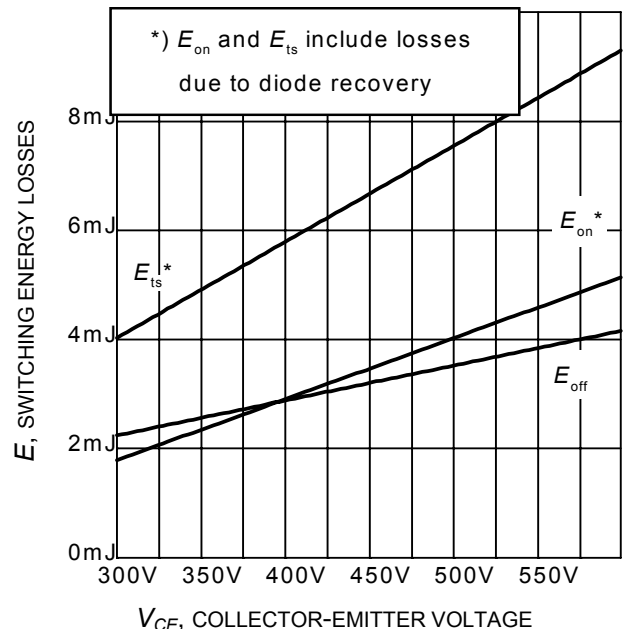
**Figure 13. Typical switching energy losses as a function of collector current**  
(inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $R_G = 5\Omega$ , Dynamic test circuit in Figure E)



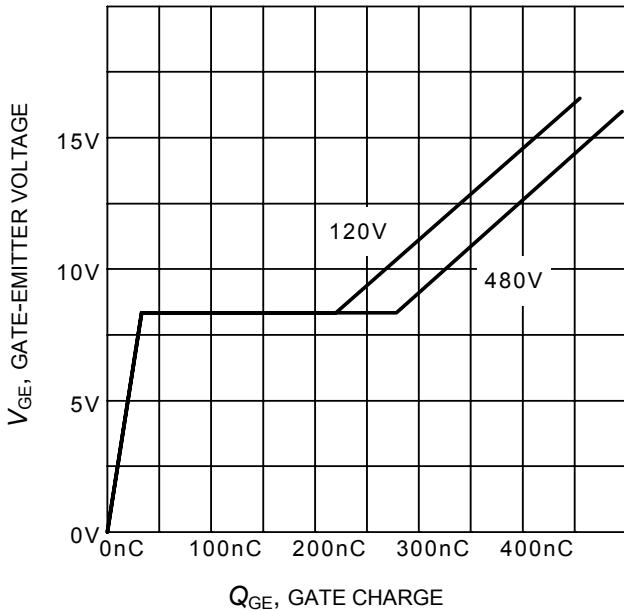
**Figure 14. Typical switching energy losses as a function of gate resistor**  
(inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 75\text{A}$ , Dynamic test circuit in Figure E)



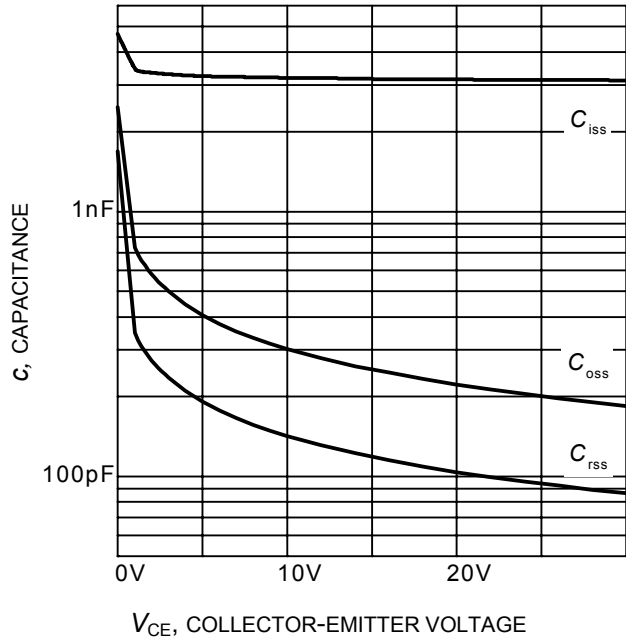
**Figure 15. Typical switching energy losses as a function of junction temperature**  
(inductive load,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 75\text{A}$ ,  $R_G = 5\Omega$ , Dynamic test circuit in Figure E)



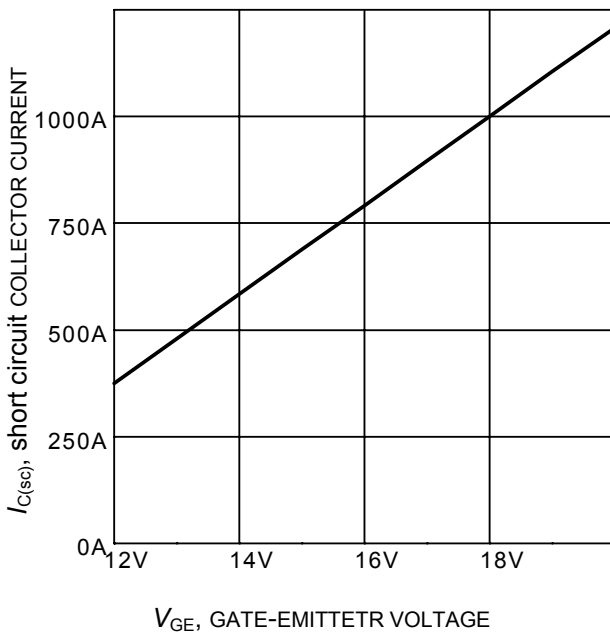
**Figure 16. Typical switching energy losses as a function of collector emitter voltage**  
(inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 75\text{A}$ ,  $R_G = 5\Omega$ , Dynamic test circuit in Figure E)



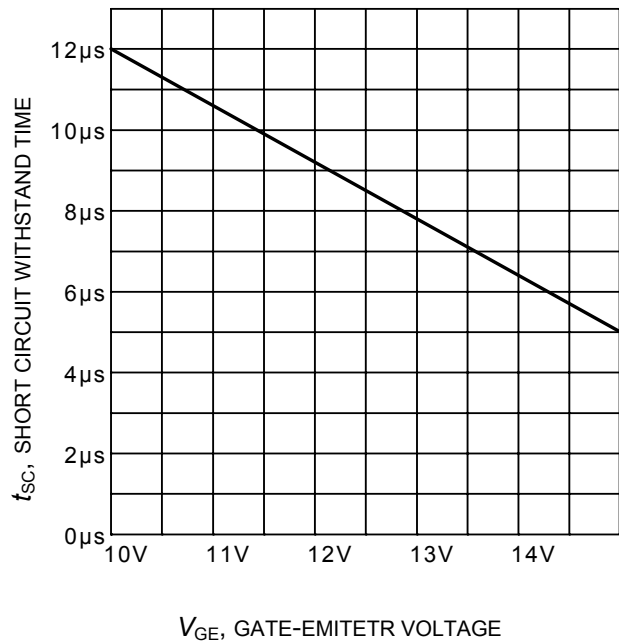
**Figure 17. Typical gate charge**  
( $I_C=75\text{ A}$ )



**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE}=0\text{V}$ ,  $f = 1\text{ MHz}$ )

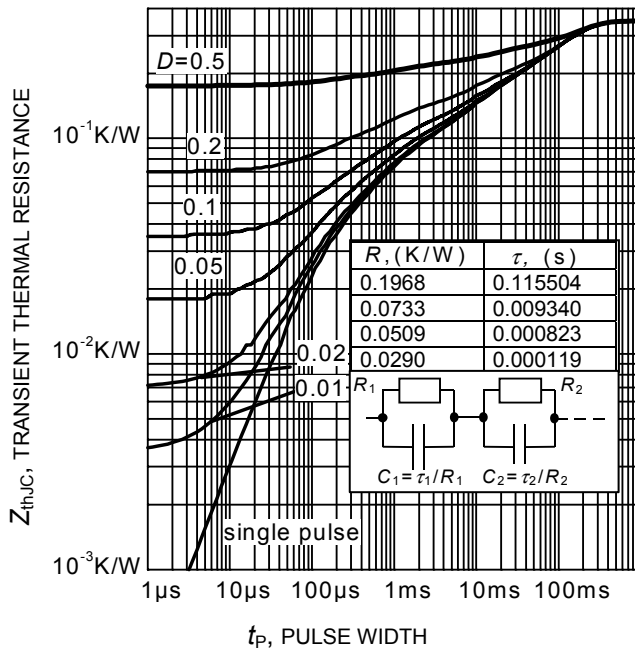


**Figure 19. Typical short circuit collector current as a function of gate-emitter voltage**  
( $V_{CE} \leq 400\text{V}$ ,  $T_J \leq 150^\circ\text{C}$ )



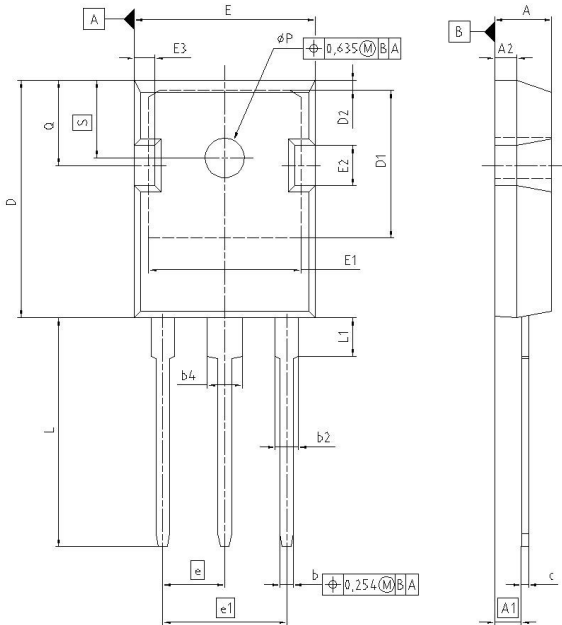
**Figure 20. Short circuit withstand time as a function of gate-emitter voltage**  
( $V_{CE}=600\text{V}$ , start at  $T_J=25^\circ\text{C}$ ,  $T_{Jmax}<150^\circ\text{C}$ )



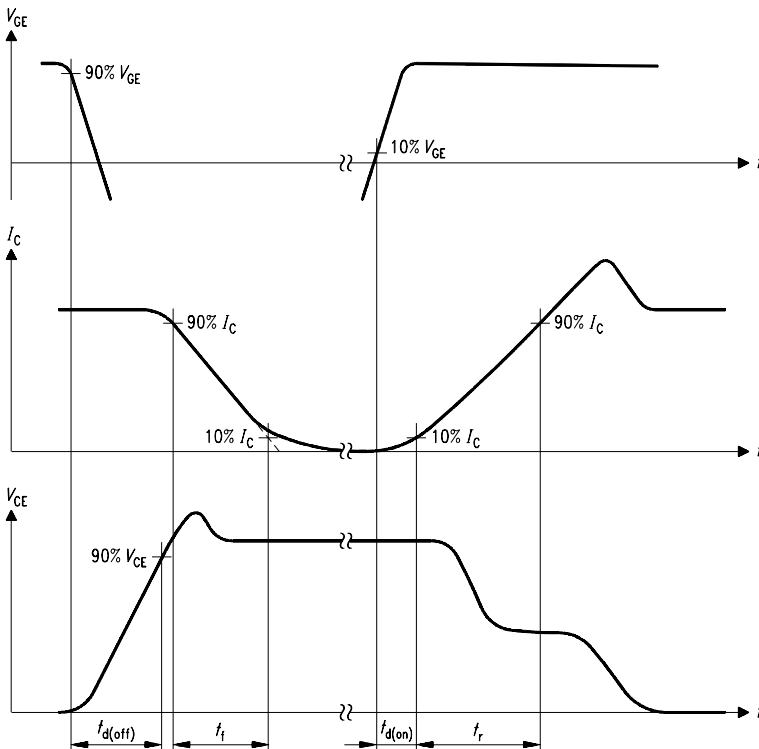


**Figure 21. IGBT transient thermal resistance**  
 $(D = t_p / T)$

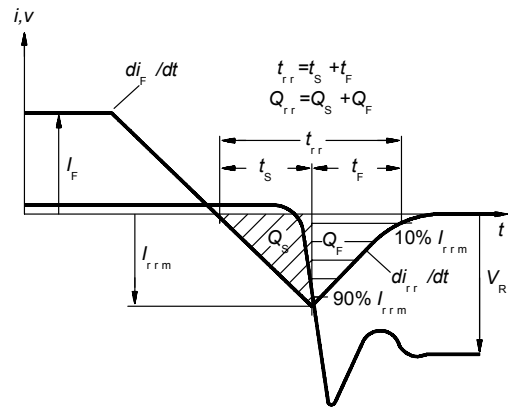
PG-TO247-3-21



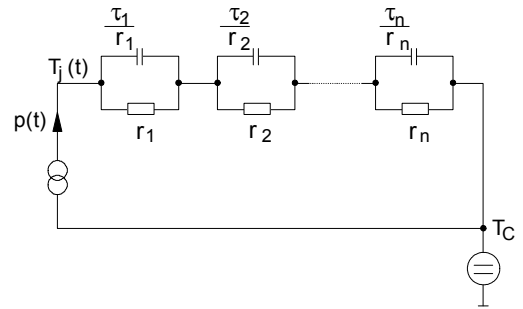
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.903	5.157	0.193	0.203
A1	2.273	2.527	0.092	0.096
A2	1.853	2.107	0.075	0.081
b	1.073	1.327	0.047	0.052
b2	1.903	2.386	0.075	0.094
b4	2.870	3.454	0.113	0.136
c	0.549	0.752	0.024	0.030
D	20.823	21.077	0.820	0.830
D1	17.323	17.831	0.682	0.702
D2	1.063	1.317	0.042	0.052
E	15.773	16.027	0.621	0.631
E1	13.893	14.147	0.547	0.557
E2	3.683	3.937	0.145	0.155
E3	1.683	1.937	0.066	0.076
e	5.450		0.215	
e1	10.900		0.430	
N	3		3	
L	20.053	20.307	0.789	0.799
L1	4.168	4.472	0.164	0.176
$\phi P$	3.559	3.661	0.140	0.144
Q	5.493	5.747	0.216	0.226
S	6.043	6.297	0.238	0.248



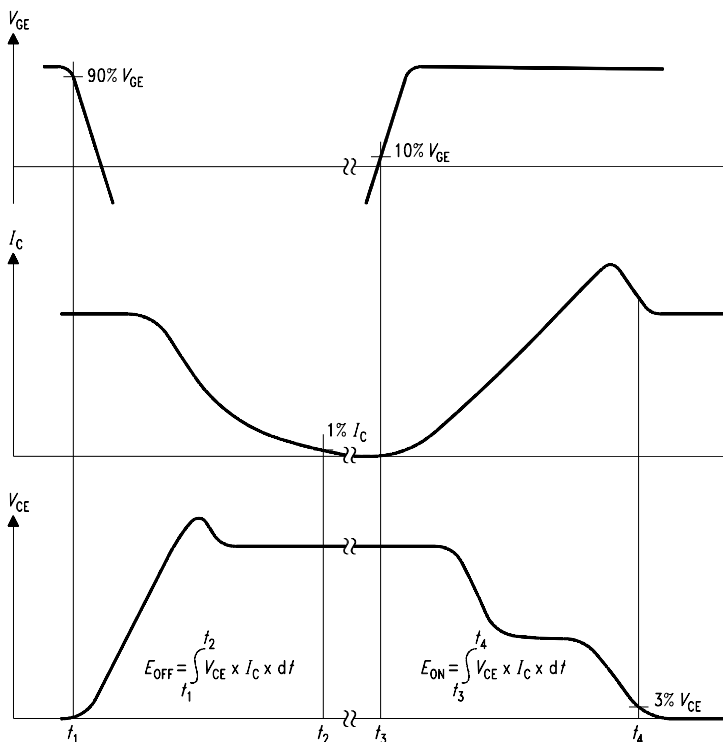
**Figure A. Definition of switching times**



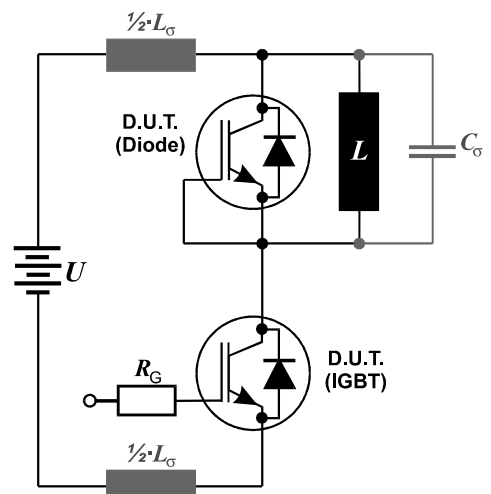
**Figure C. Definition of diodes switching characteristics**



**Figure D. Thermal equivalent circuit**



**Figure B. Definition of switching losses**



**Figure E. Dynamic test circuit**

**Edition 2006-01**

**Published by  
Infineon Technologies AG  
81726 München, Germany**

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